Features

- Trench Power LV MOSFET Technology
- Excellent Package For Heat Dissipation
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL MOSFET

Maximum Ratings

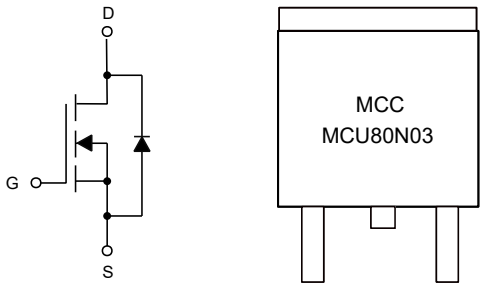
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 50°C/W Junction to Ambient(Note 2)
- Thermal Resistance: 2.1°C/W Junction to Case

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	80	A
	T_C=100°C		56	
Pulsed Drain Current(Note3)		I_{DM}	320	A
Total Power Dissipation(Note4)		P_D	71	W
Single Pulse Avalanche Energy(Note5)		E_{AS}	156	mJ

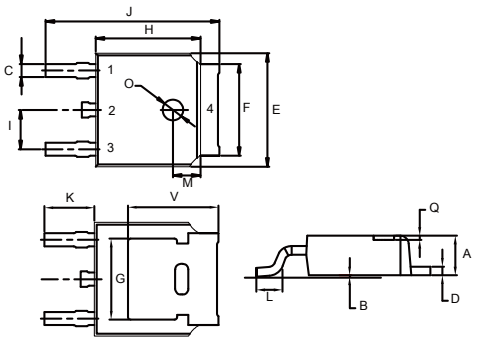
Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of RθJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25℃, V_{DD}=25V, V_{GS}=10V, L=0.5mH

Internal Structure and Marking Code



DPAK(TO-252)



1. Gate
2,4. Drain
3. Source

DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.000	0.005	0.00	0.13	
C	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
H	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
O	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	30			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	0.8	1.5	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=18A		3.1	4	mΩ
		V_{GS}=4.5V, I_D=10A		5	6	
Gate Resistance	R_g	f=1MHz, Open drain		1.7		Ω
Diode Characteristics						
Diode Forward Voltage	I_S				80	A
Continuous Body Diode Current	V_{SD}	V_{GS}=0V, I_S=20A			1.2	V
Reverse Recovery Chrage	t_{rr}	I_S=20A, dI_F/dt=230A/μs		17		ns
Reverse Recovery Time	Q_{rr}			10		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V,f=1MHz		2090		pF
Output Capacitance	C_{oss}			354		
Reverse Transfer Capacitance	C_{rss}			330		
Total Gate Charge	Q_g	V_{DS}=15V,V_{GS}=10V,I_D=20A		45		nC
Gate-Source Charge	Q_{gs}			14		
Gate-Drain Charge	Q_{gd}			7		
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V, V_{DD}=20V, I_D=2A,R_G=2.2Ω		7		ns
Turn-On Rise Time	t_r			17		
Turn-Off Delay Time	$t_{d(off)}$			37		
Turn-Off Fall Time	t_f			10		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

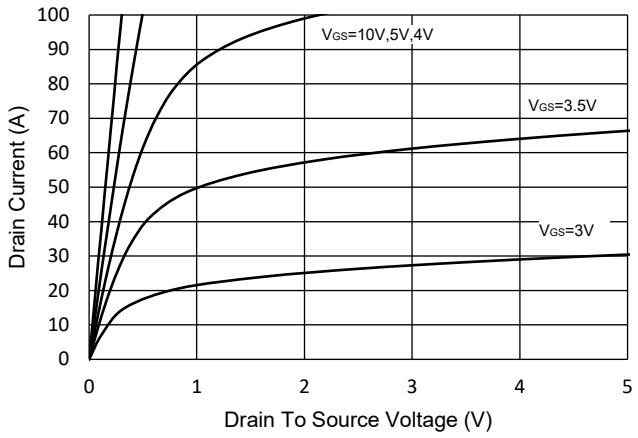


Fig.2 - Transfer Characteristic

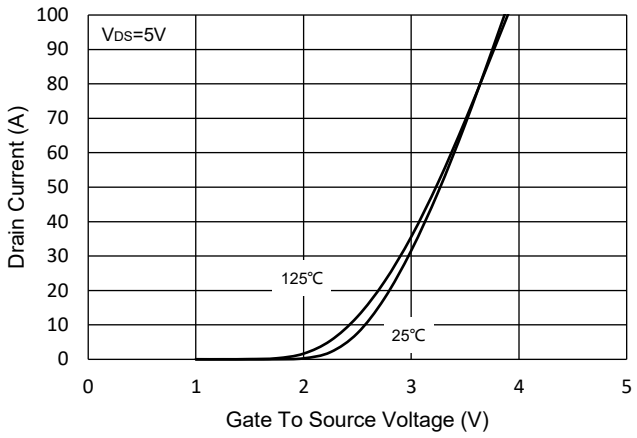


Fig.3 - $R_{DS(ON)}$ - V_{GS}

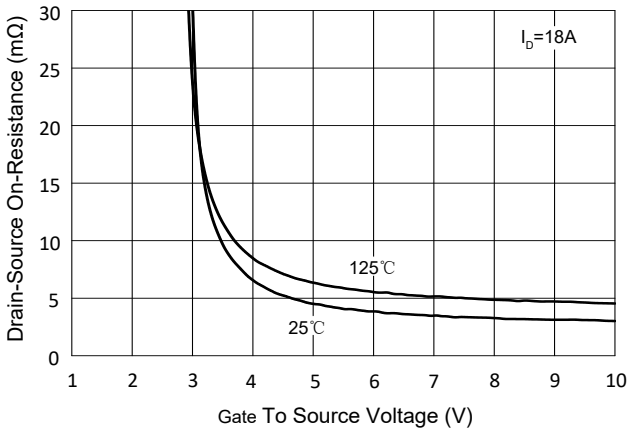


Fig.4 - $R_{DS(ON)}$ - I_D

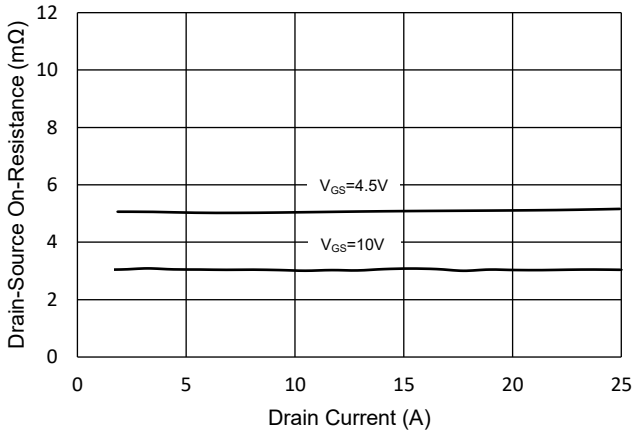


Fig.5 - Capacitance Characteristics

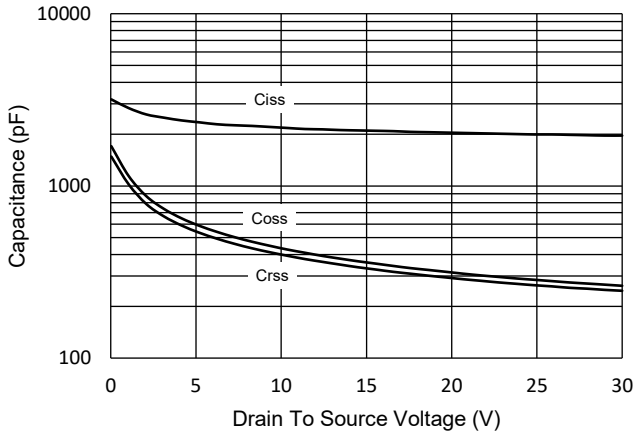
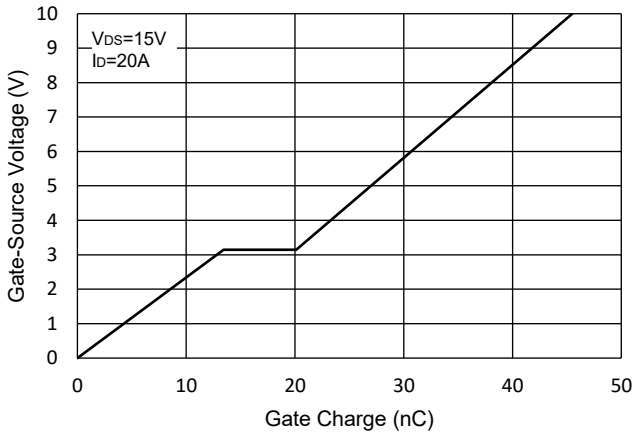


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

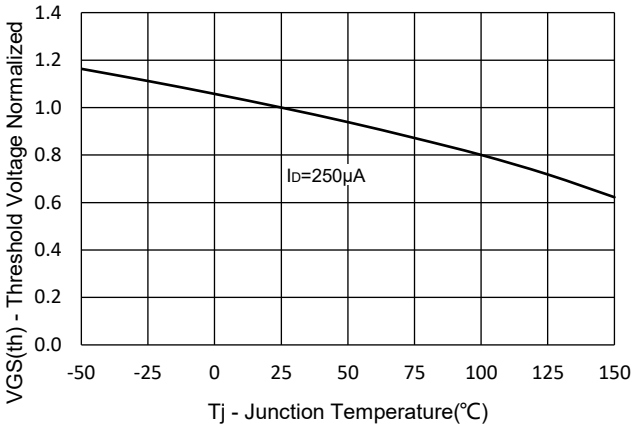


Fig.8 - Normalized On Resistance Characteristics

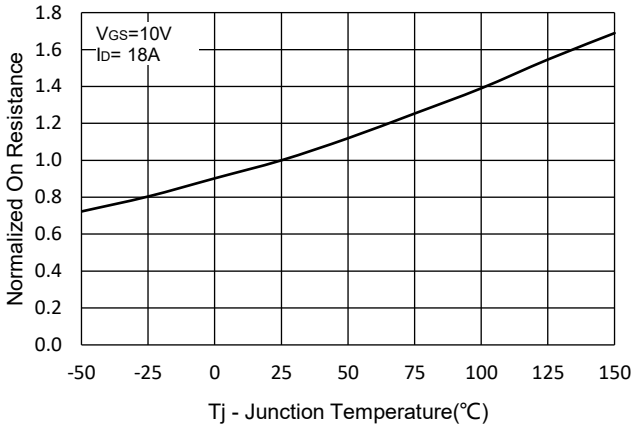


Fig.9 - I_S - V_{SD}

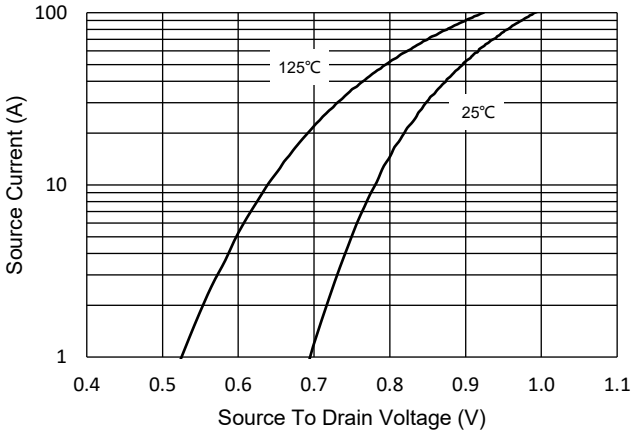


Fig.10 - Drain Current

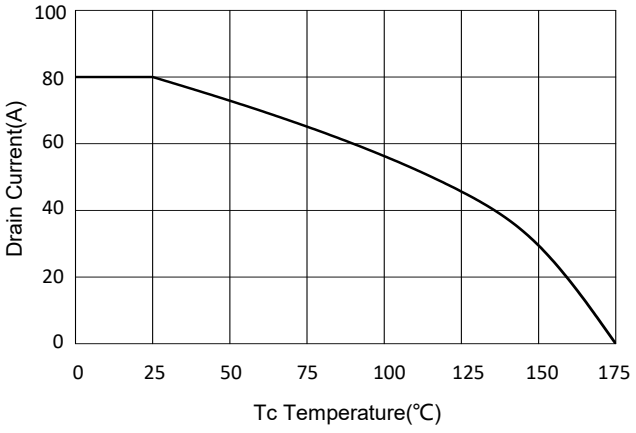
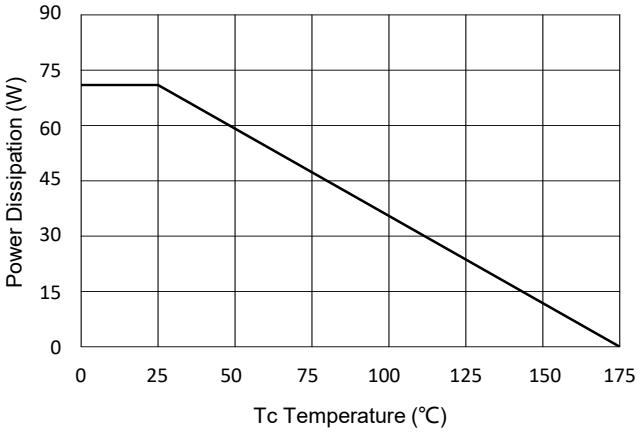


Fig.11 - PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

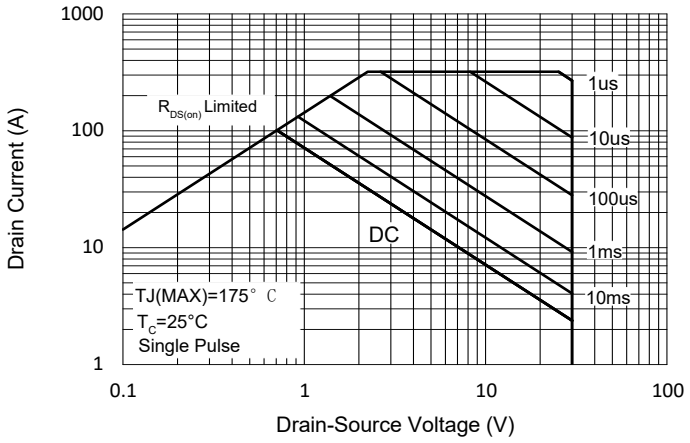
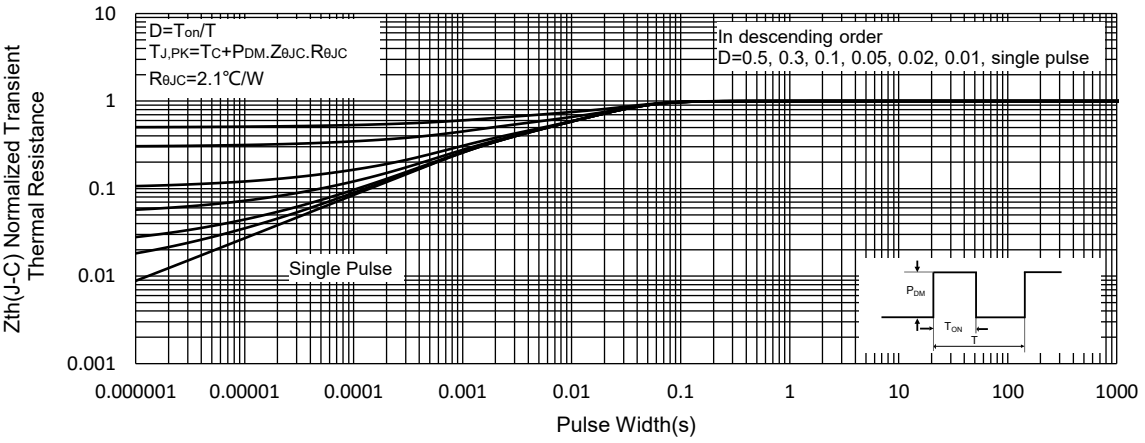


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel